NXP BT169D-L SCR datasheet

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Planar passivated very sensitive gate Silicon Controlled Rectifier in a SOT54 (TO-92) plastic package.

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Product data sheet

1. General description

Planar passivated very sensitive gate Silicon Controlled Rectifier in a SOT54 (TO-92) plastic package.

2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Very sensitive gate

3. Applications

- Ignition circuits
- Low power latching circuits
- Protection / shut-down circuits: lighting ballasts
- Protection / shut-down circuits: Switched Mode Power Supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	400	V
V_{RRM}	repetitive peak reverse voltage		-	-	400	V
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5	-	-	8	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{lead} \le 83$ °C; Fig. 2; Fig. 3	-	-	0.8	Α
Static chara	cteristics					,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 7	-	-	50	μA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	0.4	1	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.5 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ Fig. 8	-	2	4	mA





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		A K
2	G	gate		G sym037
3	К	cathode	₩₩ 	-

6. Ordering information

Table 3. Ordering information

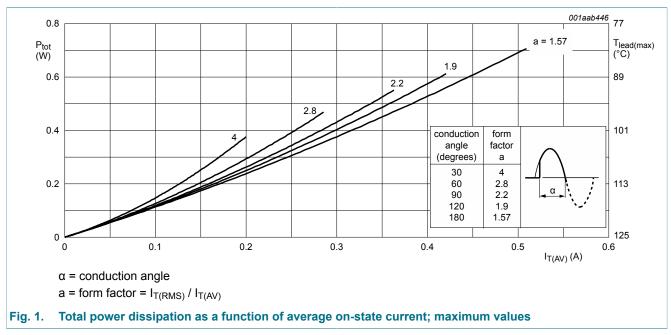
Type number	Package	kage				
	Name	Description	Version			
BT169D-L	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	400	V
V_{RRM}	repetitive peak reverse voltage		-	400	V
I _{T(AV)}	average on-state current	half sine wave; T _{lead} ≤ 83 °C; <u>Fig. 1</u>	-	0.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{lead} ≤ 83 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	0.8	А
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	-	9	А
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig. 4; Fig. 5	-	8	А
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.32	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 2 \text{ A}$; $I_G = 10 \text{ mA}$; $dI_G/dt = 100 \text{ mA}/$ μs	-	50	A/µs
I _{GM}	peak gate current		-	1	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_GM	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



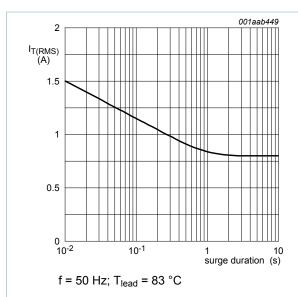
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0.6 0.6 0.4 0.2 0.50 0 50 100 150

Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents

Fig. 3. RMS on-state current as a function of lead temperature; maximum values

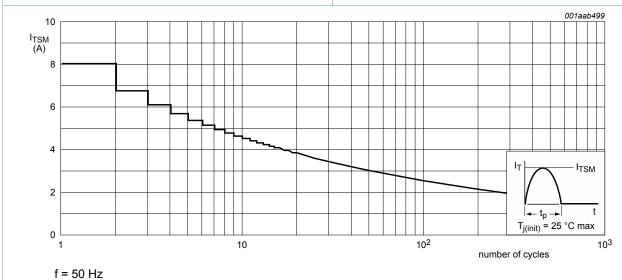
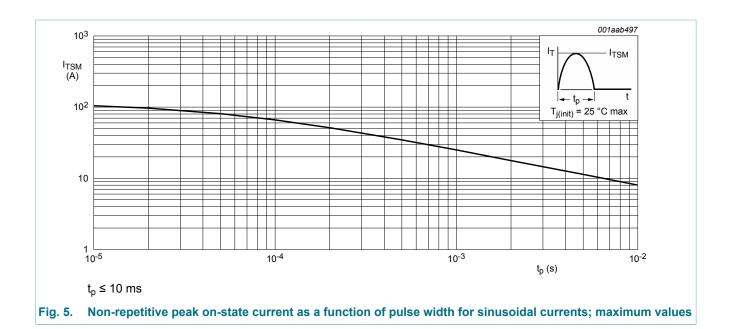


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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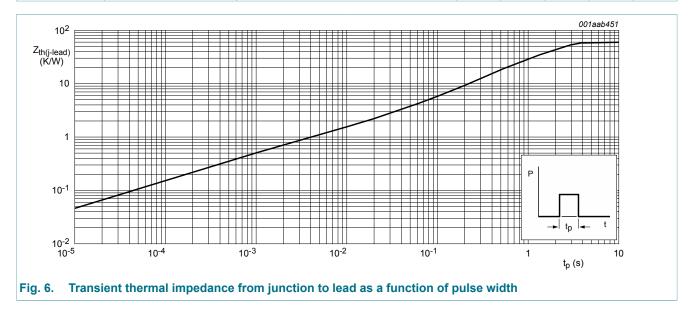


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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	Fig. 6	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



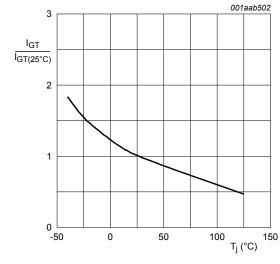
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,	'		
I _{GT}	gate trigger current	V_D = 12 V; I_T = 10 mA; T_j = 25 °C; Fig. 7	-	-	50	μΑ
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.5 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 8	-	2	4	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	0.4	1	mA
V_{T}	on-state voltage	I _T = 1.2 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.25	1.7	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	0.5	0.8	V
		$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 125 \text{ °C};$ Fig. 11	0.2	0.3	-	V
I _D	off-state current	$V_D = 400 \text{ V}; T_j = 25 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	-	2	μA
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	0.05	0.1	mA
I _R	reverse current	$V_R = 400 \text{ V}; T_j = 25 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	0.05	2	μA
		$V_R = 400 \text{ V}; T_j = 125 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	0.05	0.1	mA
Dynamic c	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 268 V; T_j = 125 °C; R_{GK} = 1 kΩ; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 12	500	800	-	V/µs
		V_{DM} = 268 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	-	25	-	V/µs



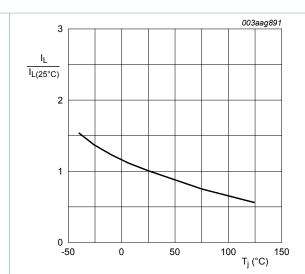
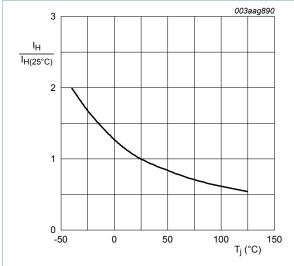


Fig. 7. Normalized gate trigger current as a function of junction temperature

Fig. 8. Normalized latching current as a function of junction temperature



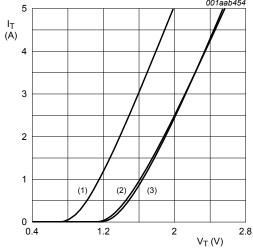


Fig. 9. Normalized holding current as a function of junction temperature

Vo = 1.067 V; Rs = 0.187 Ω (1) Tj = 125 °C; typical values (2) Tj = 125 °C; maximum values (3) Tj = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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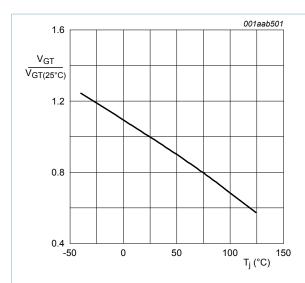


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

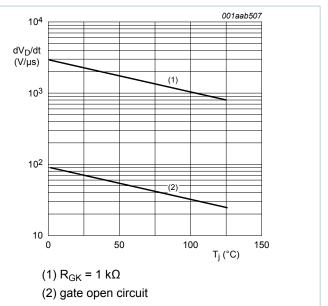
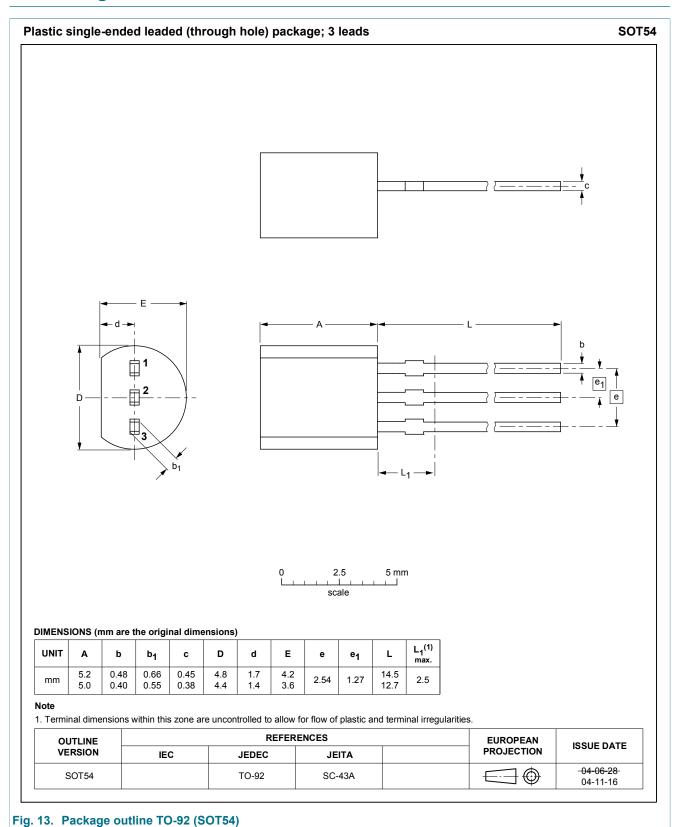


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

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10. Package outline



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